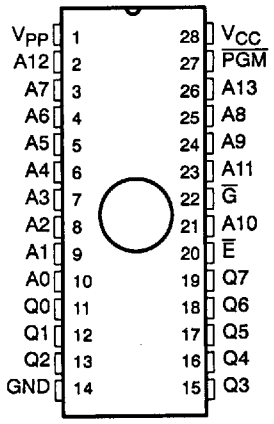
SGMS006E – AUGUST 1986 – REVISED JUNE 1995

- **Organization . . . 16K × 8**
- **Processed to MIL-STD-883, Class B**
- **Single 5-V Power Supply**
- **Pin-Compatible With Existing 64K and 128K EPROMs**
- **All Inputs/Outputs Fully TTL-Compatible**
- **Max Access/Min Cycle Times**

V_{CC} ± 5%	V_{CC} ± 10%	
'27C128-120		120 ns
	'27C128-15	150 ns
	'27C128-17	170 ns
	'27C128-20	200 ns
	'27C128-25	250 ns

- **HVCMOS Technology**
- **3-State Output Buffer**
- **Low Power Dissipation**
  - **Active . . . 138 mW Worst Case**
  - **Standby . . . 1.7 mW Worst Case (CMOS-Input Levels)**
- **400-mV Minimum DC Noise Immunity With Standard TTL Loads**
- **Military Operating Temperature Range**
  – 55°C to 125°C

J PACKAGE
(TOP VIEW)



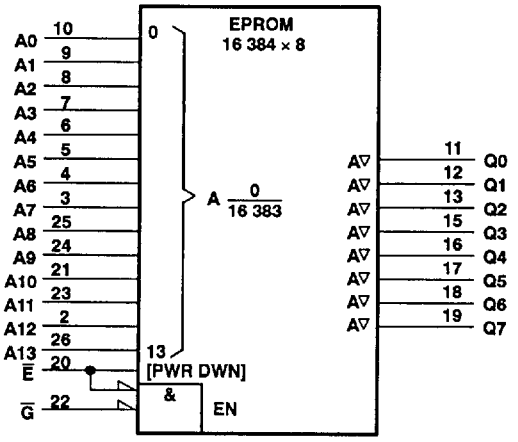
PIN NOMENCLATURE	
A0–A13	Address Inputs
$\overline{E}$	Chip Enable, Power Down
$\overline{G}$	Output Enable
GND	Ground
$\overline{PGM}$	Program
Q0–Q7	Outputs
V_{CC}	5-V Power Supply
V_{PP}	12–13-V Power Supply

description

The SMJ27C128 series is a set of 131 072-bit, ultraviolet-light erasable, electrically programmable read-only memories. These devices are fabricated using HVCMOS technology for high speed and simple interfacing with MOS and bipolar circuits. All inputs (including program data inputs) can be driven by Series 54 TTL circuits without the use of external pullup resistors. The data outputs are three-state for connecting multiple devices to a common bus. The SMJ27C128 is pin-compatible with 28-pin 128K ROMs and EPROMs. They are offered in a 600-mil dual-in-line ceramic package (J suffix) rated for operation from −55°C to 125°C.

Since these EPROMs operate from a single 5-V supply (in the read mode), they are ideal for use in microprocessor-based systems. One other (12.5 V) supply is needed for programming, but all programming signals are TTL-level. These devices are programmable by either Fast or SNAP! Pulse programming algorithms. The Fast programming algorithm uses a V_{PP} of 12.5 V and a V_{CC} of 6 V for a nominal programming time of two minutes. The SNAP! Pulse programming algorithm uses a V_{PP} of 13.0 V and a V_{CC} of 6.5 V for a nominal programming time of two seconds. For programming outside the system, existing EPROM programmers can be used. Locations can be programmed singly, in blocks, or at random.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

operation

The seven modes of operation for the SMJ27C128 are listed in the following table. The read mode requires a single 5-V supply. All inputs are TTL-level except for V_{PP} during programming (12.5 V for Fast or 13 V for SNAP! Pulse) and 12 V on A9 for signature mode.

FUNCTION (PINS)	MODE							
	READ	OUTPUT DISABLE	STANDBY	PROGRAMMING	VERIFY	PROGRAM INHIBIT	SIGNATURE MODE	
$\overline{E}$ (20)	V_{IL}	V_{IL}	V_{IH}	V_{IL}	V_{IL}	V_{IH}	V_{IL}	
G (22)	V_{IL}	V_{IH}	X‡	V_{IH}	V_{IL}	X	V_{IL}	
$\overline{PGM}$ (27)	V_{IH}	V_{IH}	X	V_{IL}	V_{IH}	X	V_{IH}	
V_{PP} (1)	V_{CC}	V_{CC}	V_{CC}	V_{PP}	V_{PP}	V_{PP}	V_{CC}	
V_{CC} (28)	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	V_{CC}	
A9 (24)	X	X	X	X	X	X	V_H§	V_H§
A0 (10)	X	X	X	X	X	X	V_{IL}	V_{IH}
Q0–Q7 (11–13, 15–19)	Data Out	Hi-Z	Hi-Z	Data In	Data Out	Hi-Z	CODE	
							MFG	DEVICE
							97	83

‡ X can be V_{IL} or V_{IH}.
§ V_H = 12 V ± 0.5 V.

read/output disable

When the outputs of two or more SMJ27C128s are connected in parallel on the same bus, the output of any device in the circuit can be read without interference from the outputs of competing devices. To read the output of the selected SMJ27C128, a low-level signal is applied to the $\overline{E}$ and $\overline{G}$ pins. All other devices in the circuit should have their outputs disabled by the application of a high-level signal to one of these pins. Output data is accessed at pins Q0 through Q7.

latchup immunity

Latchup immunity on the SMJ27C128 is achieved by the application of a minimum of 250 mA on all inputs and outputs. This current provides latchup immunity beyond any potential transients at the PC-board level when the devices are interfaced to industry-standard TTL or MOS logic devices. Input/output layout approach controls latchup without compromising performance or packing density.

For more information, see application report SMLA001, *Design Considerations; Latchup Immunity of the HVCMOS EPROM Family,* available through TI Field Sales Offices.

powerdown

Active I_{CC} supply current can be reduced from 25 mA to 500 µA (TTL-level inputs) or 300 µA (CMOS-level inputs) by applying a high input signal to the $\overline{E}$ pin. In this mode all outputs are in the high-impedance state.

erasure

Before programming, the SMJ27C128 is erased by exposing the chip through the transparent lid to a high intensity ultraviolet light (wavelength 2537 Å). EPROM erasure before programming is necessary to assure that all bits are in the logic 1 (high) state. Logic lows are programmed into the desired locations. A programmed logic low can be erased only by ultraviolet light. The recommended minimum exposure dose (UV intensity × exposure time) is 15 W•s/cm^2. A typical 12 mW/cm^2, filterless UV lamp erases the device in 21 minutes. The lamp should be located about 2.5 cm above the chip during erasure. After erasure, all bits are in the high state. It should be noted that normal ambient light contains the correct wavelength for erasure. Therefore, when using the SMJ27C128, the window should be covered with an opaque label.

SNAP! Pulse programming

The 128K EPROM can be programmed using the TI SNAP! Pulse programming algorithm illustrated by the flowchart in Figure 1. The TI SNAP! Pulse programming algorithm can reduce programming time to two seconds. Actual programming time varies as a function of the programming used.

Data is presented in parallel (eight bits) on pins Q0 to Q7. Once addresses and data are stable, $\overline{PGM}$ is pulsed.

The SNAP! Pulse programming algorithm uses initial pulses of 100 µs followed by a byte verification to determine when the addressed byte has been successfully programmed. Up to ten 100-µs pulses per byte are provided before a failure is recognized.

The programming mode is achieved when V_{PP} = 13 V, V_{CC} = 6.5 V, $\overline{G}$ = V_{IH}, and $\overline{E}$ = V_{IL}. More than one device can be programmed when the devices are connected in parallel. Locations can be programmed in any order. When the SNAP! Pulse programming routine is complete, all bits are verified with V_{CC} = V_{PP} = 5 V.

Fast programming

The 128K EPROM can be programmed using the Fast programming algorithm illustrated by the flowchart in Figure 2. During Fast programming, data is presented in parallel (eight bits) on pins Q0 through Q7. Data is presented in parallel (eight bits) on pins Q0 to Q7. Once addresses and data are stable, $\overline{PGM}$ is pulsed.

Fast programming (continued)

The programming mode is achieved when V_{PP} = 12.5 V, V_{CC} = 6 V, $\overline{G}$ = V_{IH}, $\overline{PGM}$ = V_{IL}, and $\overline{E}$ = V_{IL}. More than one SMJ27C128 can be programmed when the devices are connected in parallel. Locations can be programmed in any order.

Programming uses two types of programming pulses: prime and final. The length of the prime pulse is 1 millisecond; this pulse is applied up to 25 times. After each prime pulse, the byte being programmed is verified. If the correct data is read, the final programming pulse is applied; if correct data is not read, an additional 1 millisecond pulse is applied up to 25 times. The final programming pulse is 3X long. This sequence of programming and verification is performed at V_{CC} = 6 V and V_{PP} = 12.5 V. When the full Fast programming routine is complete, all bits are verified with V_{CC} = V_{PP} = 5 V (see Figure 2).

program inhibit

Programming can be inhibited by maintaining a high level input on the $\overline{E}$ or $\overline{PGM}$ pin.

program verify

Programmed bits can be verified with V_{PP} = 12.5 V when $\overline{G}$ = V_{IL}, $\overline{E}$ = V_{IL}, and $\overline{PGM}$ = V_{IH}.

signature mode

The signature mode provides access to a binary code identifying the manufacturer and type. This mode is activated when A9 (pin 24) is forced to 12 V ± 0.5 V. Two identifier bytes are accessed by A0 (pin 10); i.e., A0 = V_{IL} accesses the manufacturer code, which is output on Q0–Q7; A0 = V_{IH} accesses the device code, which is output on Q0–Q7. All other addresses must be held at V_{IL}. Each byte possesses odd parity on bit Q7. The manufacturer code for these devices is 97, and the device code is 83.

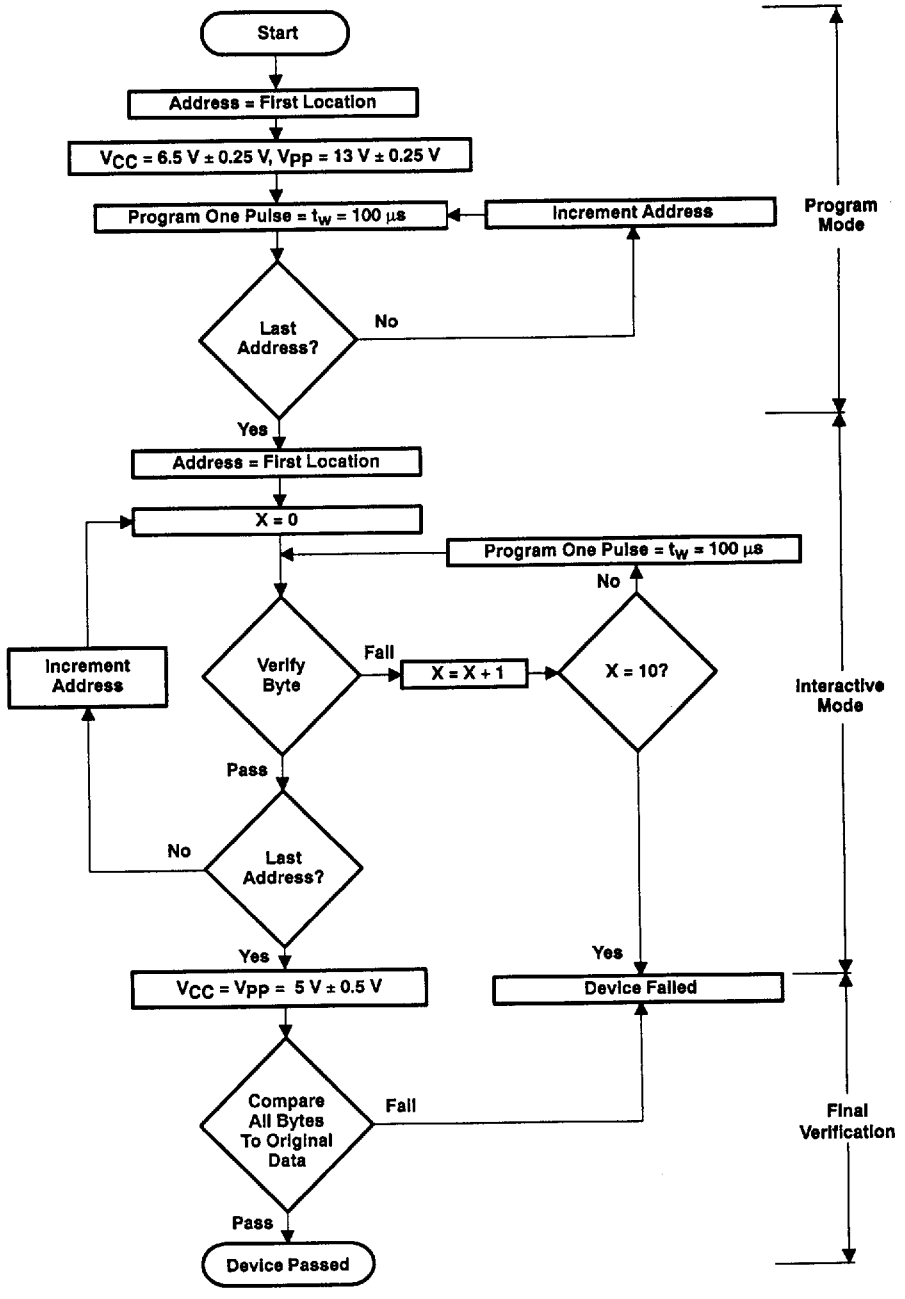


Figure 1. SNAP! Pulse Programming Flowchart

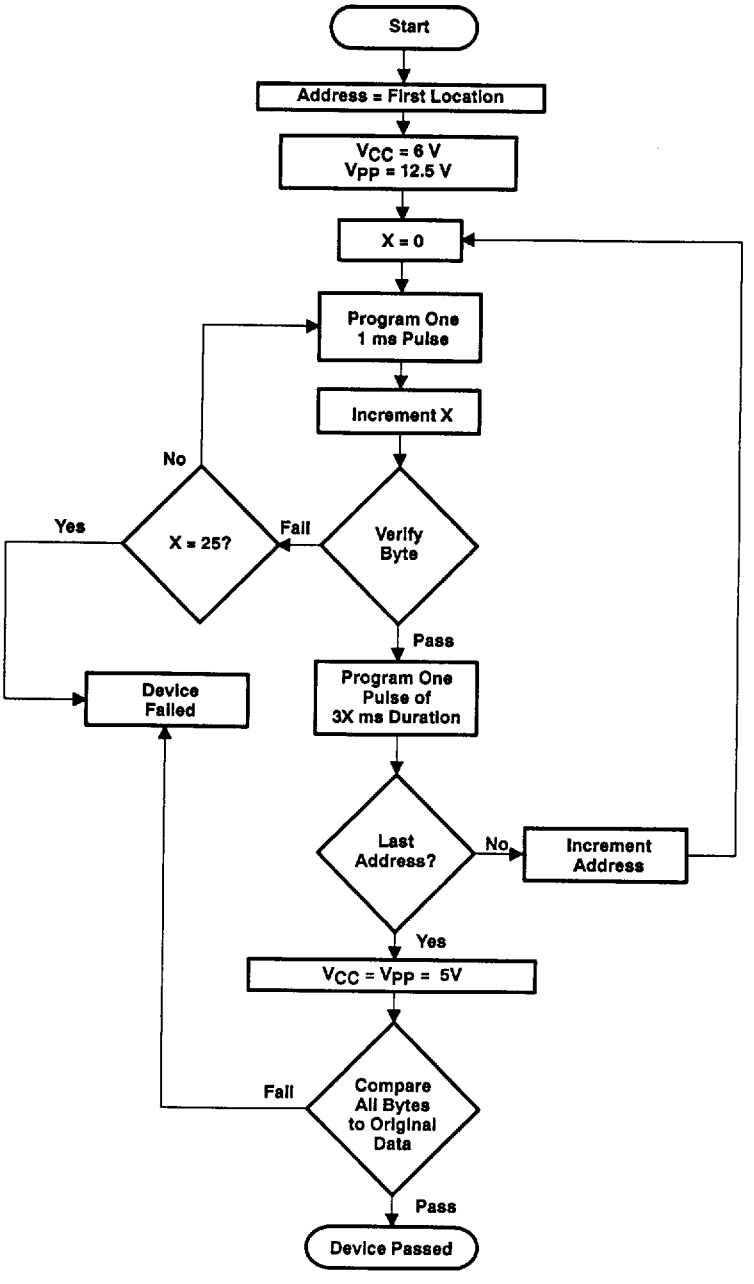


Figure 2. Fast Programming Flowchart

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} (see Note 1) ..... −0.6 V to 7 V
Supply voltage range, V_{PP} (see Note 1) ..... −0.6 V to 14 V
Input voltage range (see Note 1), All inputs except A9 ..... −0.6 V to 6.5 V
A9 ..... −0.6 V to 13.5 V
Output voltage range (see Note 1) ..... −0.6 V to V_{CC} + 1 V
Minimum operating free-air temperature, T_A ..... −55° C
Maximum operating case temperature ..... 125° C
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to GND.

recommended operating conditions

				'27C128-120			'27C128-15 '27C128-17 '27C128-20 '27C128-25			UNIT
				MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage	Read mode (see Note 2)		4.75	5	5.25	4.5	5	5.5	V
		Fast programming algorithm		5.75	6	6.25	5.75	6	6.25	V
		SNAP! Pulse programming algorithm		6.25	6.50	6.75	6.25	6.5	6.75	V
V_{PP}	Supply voltage	Read mode (see Note 3)		V_{CC}−0.6		V_{CC}+0.6	V_{CC}−0.6		V_{CC}+0.6	V
		Fast programming algorithm		12	12.5	13	12	12.5	13	V
		SNAP! Pulse programming algorithm		12.75	13	13.25	12.75	13	13.25	V
V_{IH}	High-level input voltage		TTL	2		V_{CC} + 1	2		V_{CC} + 1	V
			CMOS	V_{CC}−0.2		V_{CC} + 1	V_{CC}−0.2		V_{CC} + 1	V
V_{IL}	Low-level input voltage		TTL	−0.5		0.8	−0.5		0.8	V
			CMOS	−0.5		0.2	−0.5		0.2	V
T_A	Operating free-air temperature			−55			−55			°C
T_C	Operating case temperature					125			125	°C

NOTES: 2. V_{CC} must be applied before or at the same time as V_{PP} and removed after or at the same time as V_{PP}. The device must not be inserted into or removed from the board when V_{PP} or V_{CC} is applied.

3. V_{PP} can be connected to V_{CC} directly (except in the program mode). V_{CC} supply current in this case is I_{CC} + I_{PP}.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature

PARAMETER			TEST CONDITIONS	MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage		I_{OH} = −400 mA	2.4			V
V_{OL}	Low-level output voltage		I_{OL} = 2.1 mA			0.4	V
I_I	Input current (leakage)		V_I = 0 V to 5.5 V			±1	µA
I_O	Output current (leakage)		V_O = 0 V to V_{CC}			±1	µA
I_{PP1}	V_{PP} supply current		V_{PP} = V_{CC} = 5.5 V			100	µA
I_{PP2}	V_{PP} supply current (during program pulse) (see Note 4)		V_{PP} = 13 V		35	50	mA
I_{CC1}	V_{CC} supply current (standby)	TTL-input level	V_{CC} = 5.5 V, $\overline{E}$ = V_{IH}			500	µA
		CMOS-input level	V_{CC} = 5.5 V, $\overline{E}$ = V_{CC}			300	µA
I_{CC2}	V_{CC} supply current (active)		V_{CC} = 5.5 V, $\overline{E}$ = V_{IL}, t_c = minimum cycle time, outputs open		10	25	mA

† Typical values are at T_A = 25°C and nominal voltages.
NOTE 4: This parameter has been characterized at 25°C and is not tested.

capacitance over recommended ranges of supply voltage and operating free-air temperature, f = 1 MHz (see Note 5)

PARAMETER		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
C_i	Input capacitance	V_I = 0 V, f = 1 MHz		6	10	pF
C_o	Output capacitance	V_O = 0 V, f = 1 MHz		8	14	pF

† Typical values are at T_A = 25°C and nominal voltages.
NOTE 5: Capacitance measurements are made on sample basis only.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (see Notes 4 and 5)

PARAMETER		TEST CONDITIONS (SEE NOTES 4 AND 5)	'27C128-120		'27C128-15		'27C128-17		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
$t_{a(A)}$	Access time from address	See Figure 3		120		150		170	ns
$t_{a(E)}$	Access time from chip enable			120		150		170	ns
$t_{en(G)}$	Output enable time from $\overline{G}$			50		70		70	ns
t_{dis}	Output disable time from $\overline{G}$ or $\overline{E}$, whichever occurs first†		0	50	0	50	0	50	ns
$t_{v(A)}$	Output data valid time after change of address, $\overline{E}$, or $\overline{G}$, whichever occurs first†		0		0		0		ns

PARAMETER		TEST CONDITIONS (SEE NOTES 4 AND 5)	'27C128-20		'27C128-25		UNIT
			MIN	MAX	MIN	MAX	
$t_{a(A)}$	Access time from address	See Figure 3		200		250	ns
$t_{a(E)}$	Access time from chip enable			200		250	ns
$t_{en(G)}$	Output enable time from $\overline{G}$			75		100	ns
t_{dis}	Output disable time from $\overline{G}$ or $\overline{E}$, whichever occurs first‡		0	60	0	60	ns
$t_{v(A)}$	Output data valid time after change of address, $\overline{E}$, or $\overline{G}$, whichever occurs first‡		0		0		ns

‡ Value calculated from 0.5 V delta to measured level. This parameter is only sampled and not production-tested.

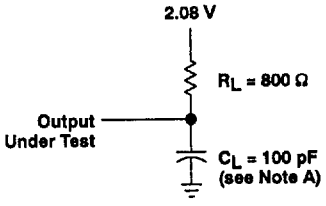
recommended timing requirements for programming: V_{CC} = 6 V and V_{PP} = 12.5 V (Fast) or V_{CC} = 6.5 and V_{PP} =13 V (SNAP! Pulse), T_A = 25°C (see Note 6)

			MIN	NOM	MAX	UNIT
t_{dis}	Disable time, output from $\overline{G}$		0		130	ns
t_{enG}	Enable time, output from $\overline{G}$				150	ns
$t_{h(A)}$	Hold time, address		0			µs
$t_{h(D)}$	Hold time, data		2			µs
$t_{w(IPGM)}$	Pulse duration, initial program	Fast programming algorithm	0.95	1	1.05	ms
		SNAP! Pulse programming algorithm	95	100	105	µs
$t_{w(FPGM)}$	Pulse duration, final	Fast programming only	2.85		78.75	ms
$t_{su(A)}$	Setup time, address		2			µs
$t_{su(G)}$	Setup time, $\overline{G}$		2			µs
$t_{su(D)}$	Setup time, data		2			µs
$t_{su(VPP)}$	Setup time, V_{PP}		2			µs
$t_{su(VCC)}$	Setup time, V_{CC}		2			µs
$t_{su(E)}$	Setup time, $\overline{E}$		2			µs

NOTES: 6. For all switching characteristics and timing measurements input pulse levels are 0.4 V to 2.4 V. Timing measurements are made at 2.0 V for logic high and 0.8 V for logic low for both inputs and outputs.

7. Common test conditions apply for t_{dis} except during programming.

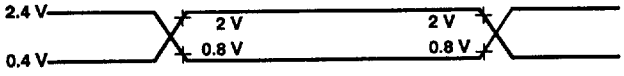
PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes probe and fixture capacitance.

Figure 3. Output Load Circuit

AC testing input/output wave forms



AC testing inputs are driven at 2.4 V for logic high and 0.4 V for logic low. Timing measurements are made at 2 V for logic high and 0.8 V for logic low for both inputs and outputs.

PARAMETER MEASUREMENT INFORMATION

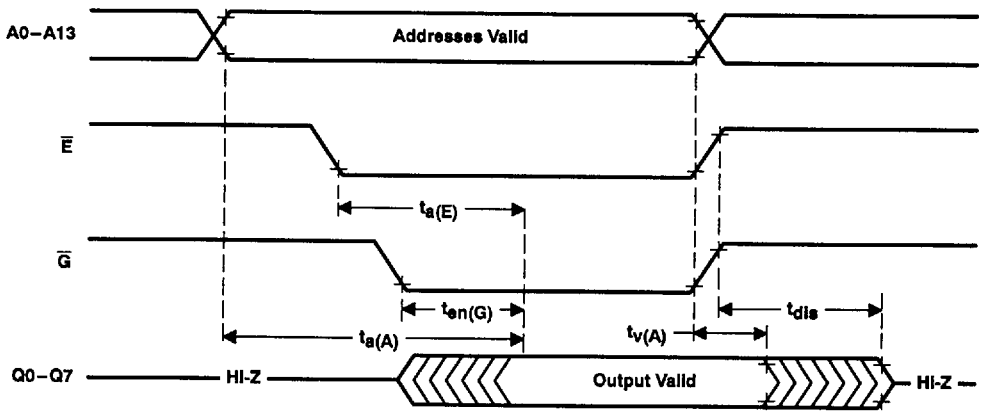


Figure 4. Read-Cycle Timing

PARAMETER MEASUREMENT INFORMATION

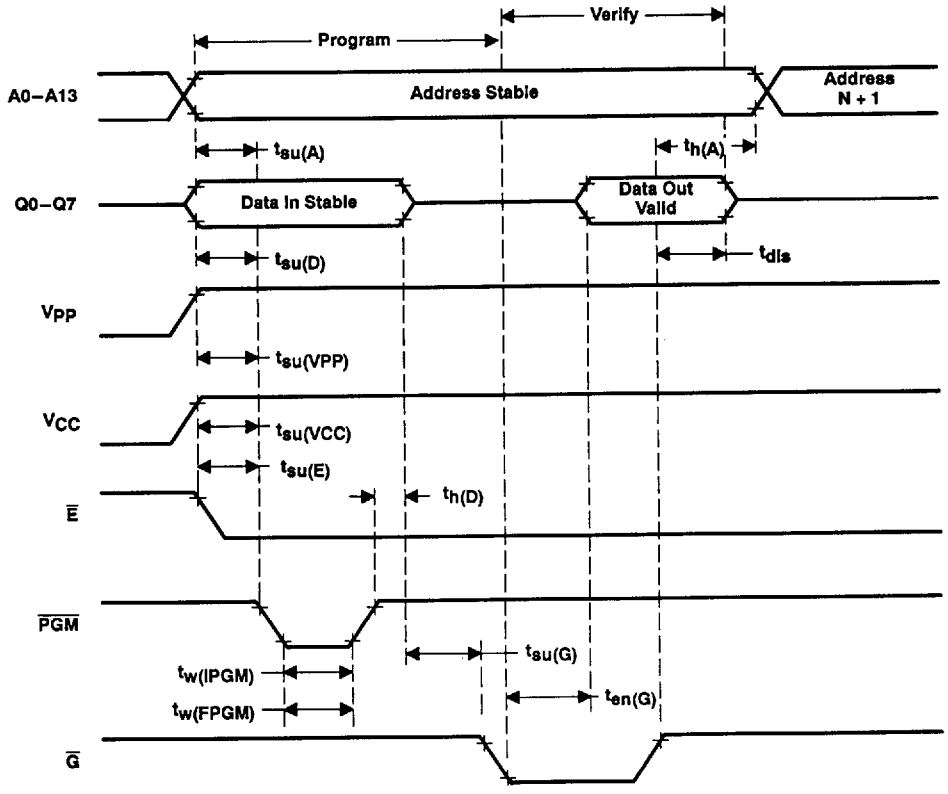


Figure 5. Program-Cycle Timing